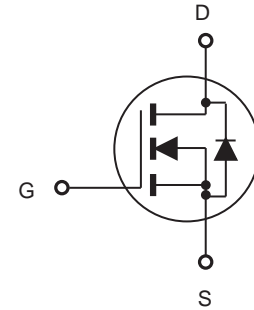


## N-Channel Enhancement Mode Field Effect Transistor

### FEATURES

- 250V, 6.7A,  $R_{DS(ON)} = 450m\Omega$  @  $V_{GS} = 10V$ .
- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- Lead free product is acquired.
- TO-251 & TO-252 package.



### ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	250	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Drain Current-Continuous	$I_D$	6.7	A
Drain Current-Pulsed <sup>a</sup>	$I_{DM}$	26	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above $25^\circ\text{C}$	$P_D$	46	W
		0.37	W/ $^\circ\text{C}$
Operating and Store Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.7	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^\circ\text{C/W}$

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# CEDF634/CEUF634

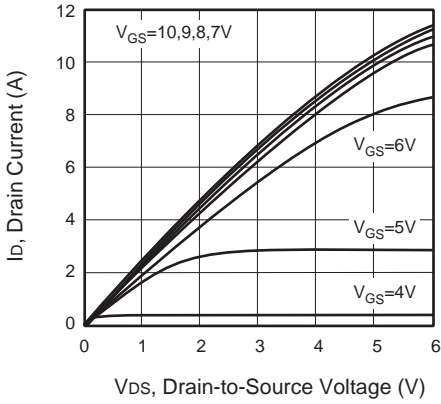


Figure 1. Output Characteristics

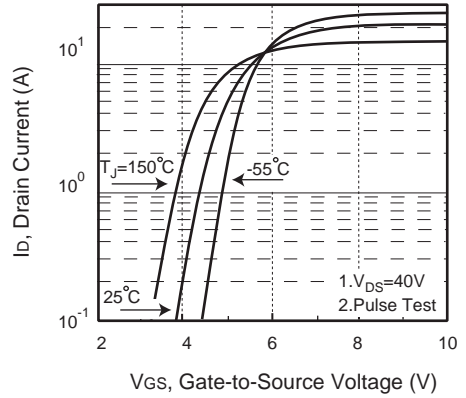


Figure 2. Transfer Characteristics

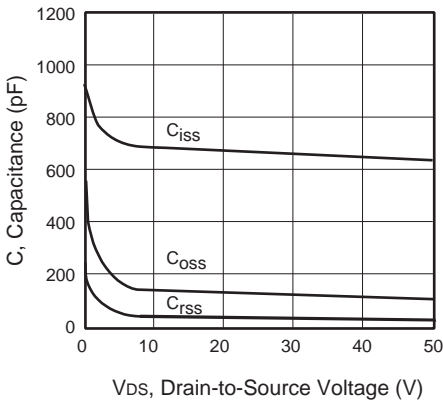


Figure 3. Capacitance

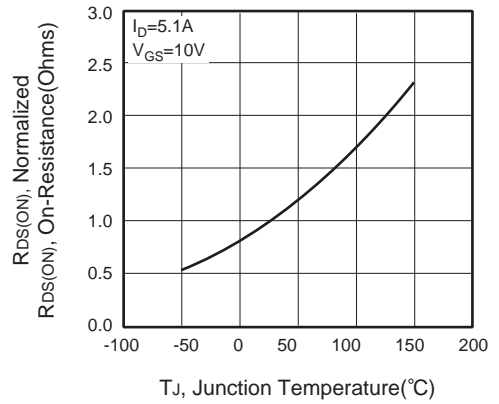


Figure 4. On-Resistance Variation with Temperature

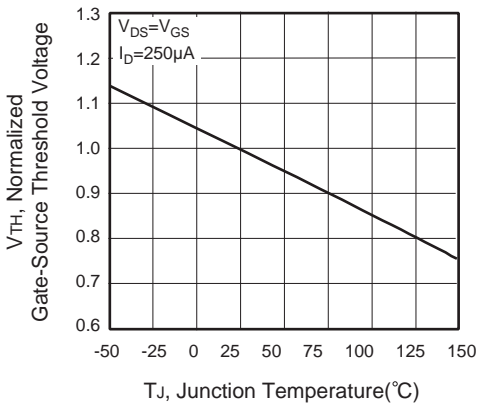


Figure 5. Gate Threshold Variation with Temperature

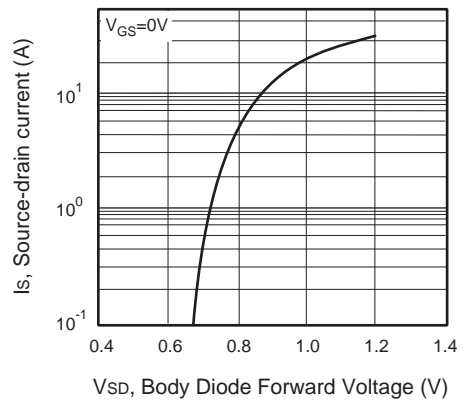


Figure 6. Body Diode Forward Voltage Variation with Source Current



# CEDF634/CEUF634

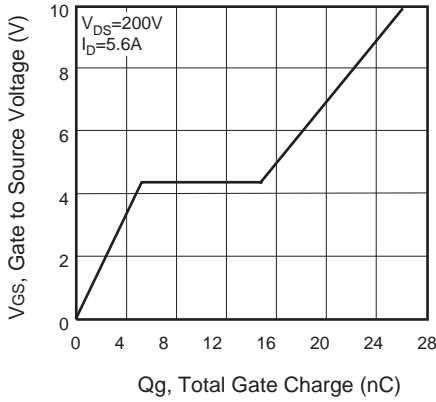


Figure 7. Gate Charge

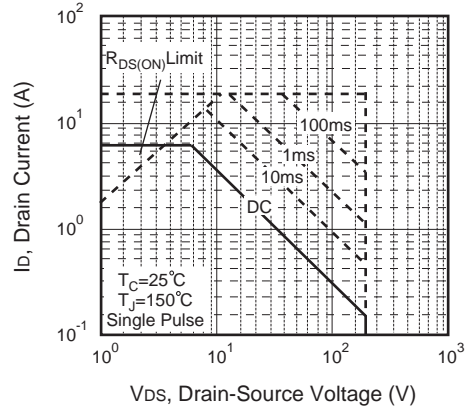


Figure 8. Maximum Safe Operating Area

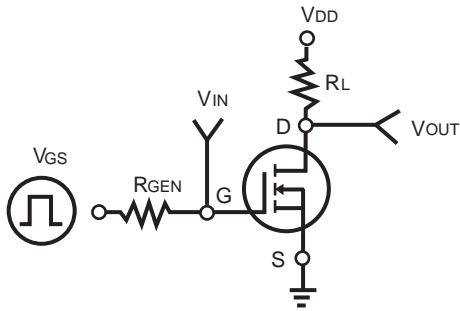


Figure 9. Switching Test Circuit

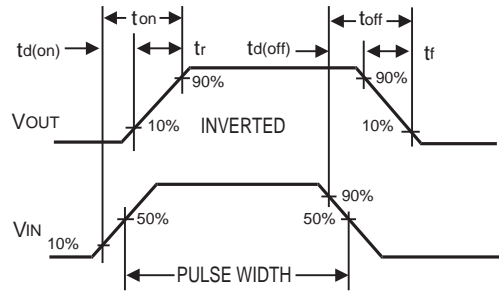


Figure 10. Switching Waveforms

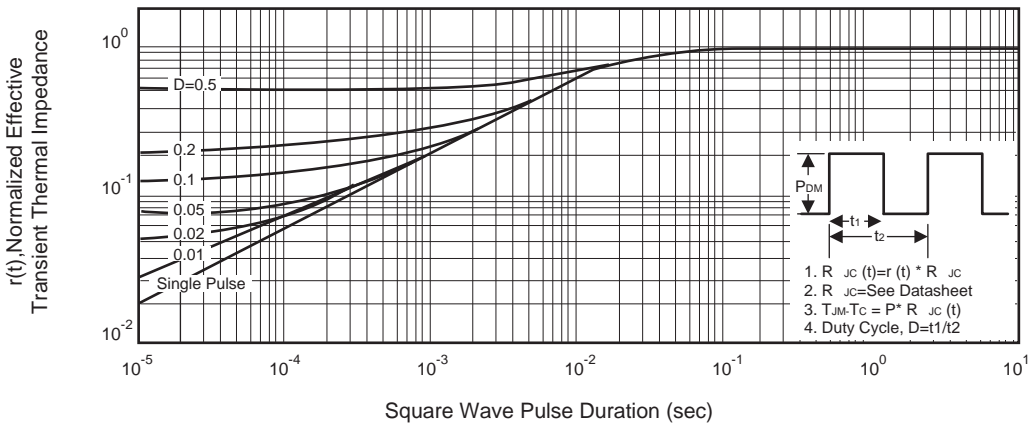


Figure 11. Normalized Thermal Transient Impedance Curve